

# Readout Design Concept for Light Detection in Noble Liquid TPCs using Large Capacitance SiPMs

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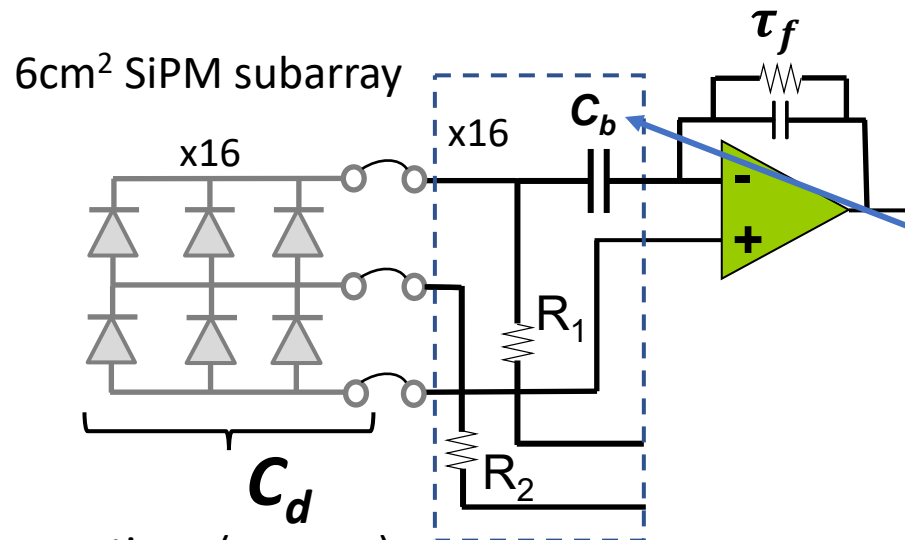
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# Outline

- The need for large area SiPM light detectors:
  - nEXO SiPM area  $\sim 4.6 \text{ m}^2$  ; DUNE  $\sim$  tens of  $\text{m}^2$
- There is a large mismatch between the “giant” SiPM capacitance  $C_d$  (many nanofarads) and a tiny input transistor gate capacitance  $C_g$  (a few picofarads).
- Conventional approach: Transfer all the SiPM avalanche charge onto an (“current”) amplifier – not optimal for  $C_d/C_g \gg 1$
- A different approach: Transfer only a charge that we can “naturally see”, due to sharing among the capacitances, onto the input transistor gate.
- Advantages: instead of a “giant” (de)coupling capacitor to close the signal circuit, a much smaller capacitor is sufficient; lower power dissipation; SiPM and electronic gain calibration.
- Single and multiple photoelectron response, S/N and timing resolution are demonstrated for 20 nF ( $6 \text{ cm}^2$ ) SiPM subarrays operated at low temperature (LN2).

# “Giant” SiPM Capacitance

Technology	“HPK”	“FBK”
$C/A$ [nF/cm <sup>2</sup> ]	3.5	8.5
$V_{op}$ [V]	60	30
$C_{6cm^2}$ [nF]	<b>21</b>	<b>51</b>
$C_{2s}$ [nF]	<b>5</b>	<b>12.5</b>
$V_{2s}$ [V]	120	60



Why “*Giant*”?

SiPM capacitance  $C_d$  (in any practical arrangement) is much higher than in any known detector

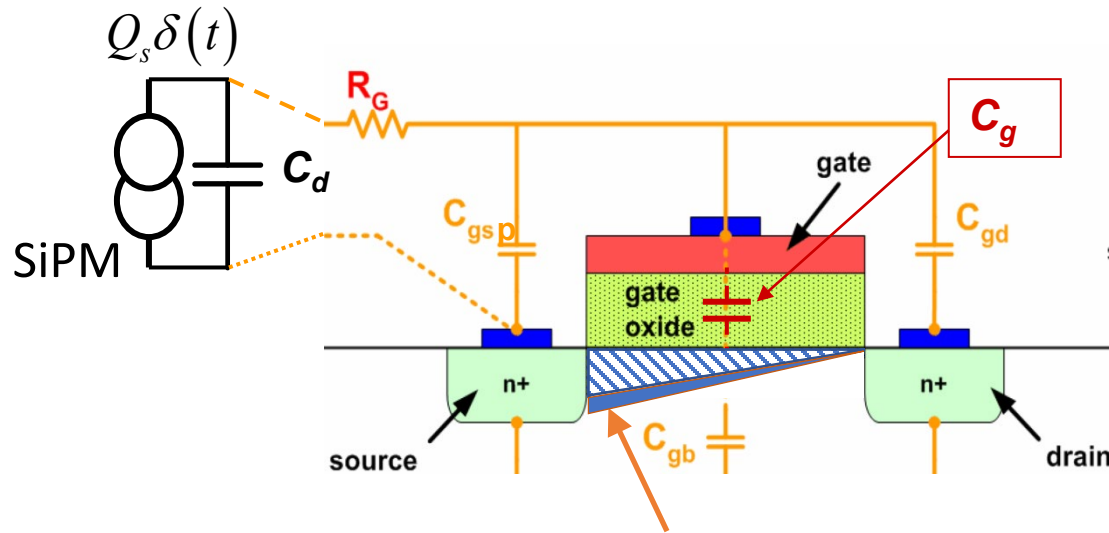
- $C_d$  is large, but so is the charge/pe,  $Q_s \sim 0.4$  pC ( $2.4 \times 10^6 e^-$ )
- *The charge is bound to that giant capacitance: can we “see” it??*
- *How to “extract” the charge while applying the bias to SiPMs?*
- *Does  $C_b$ , the decoupling (radio pure) HV capacitor have also to be “giant”?*

Assumptions (approx.):

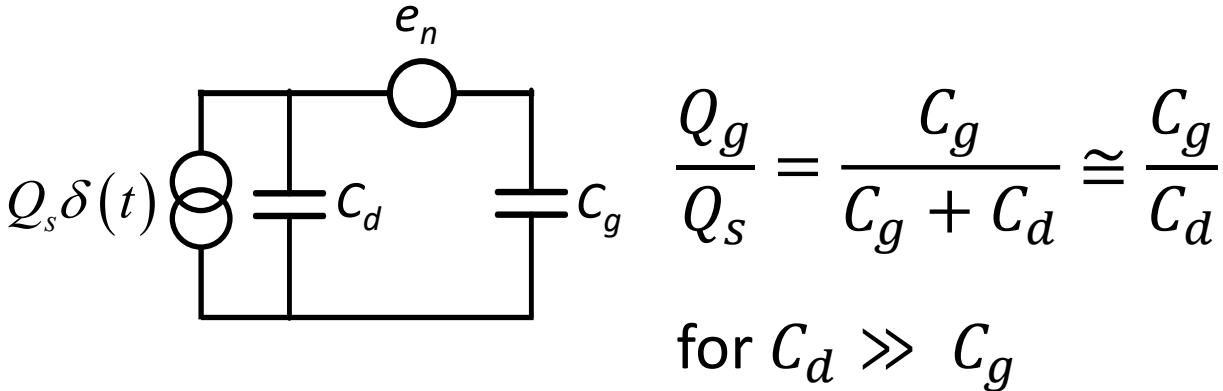
- Number of readout channels in nEXO  $\sim 8000 \times 6\text{cm}^2$  for a SiPM area of  $\sim 4.8 \text{ m}^2$

# SiPM – transistor capacitance mismatch

- how much of the avalanche signal charge do we really “see”?



“useful” charge:  $Q_g$  modulates the channel and with transistor noise determines S/N



Example:

$$C_d = 10 \text{ nF}$$

$$C_g = 25 \text{ pF (very large transistor)}$$

$$(Q_g/Q_s) = (C_g/C_d) = 1/400$$

We “see” only **1/400** of the SiPM avalanche charge.

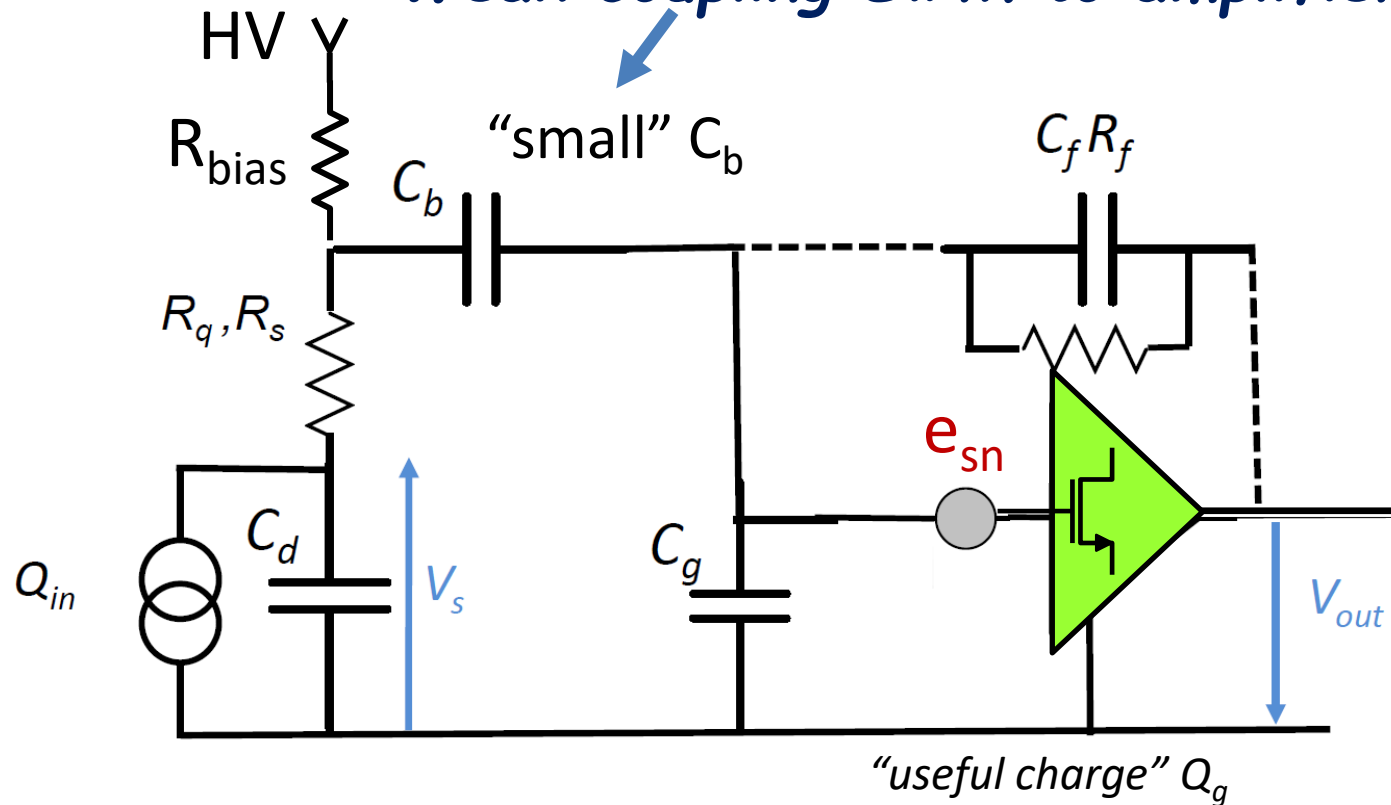
A long way to an ideal capacitance match:

$$(Q_g/Q_s)_{\max} = 1/2$$

$$\text{for } (C_g/C_d) = 1$$

Should we think of something different?

*Weak coupling SiPM to amplifier*



$$\left(\frac{S}{N}\right)_n = \frac{Q_{in}/C_d}{e_{sn}/t_p^{1/2}} \cdot \frac{n}{1 + C_g/C_b + n^2 C_g/C_d}$$

$n$  = series connection  
(slide 7,  $n=2$ )

$$\frac{Q_g}{Q_{in}} = \frac{C_g}{C_d} \cdot \frac{1}{1 + \frac{C_g}{C_b} + \frac{C_g}{C_d}}$$

$$\sim 1 \text{ for } \frac{C_d}{C_b} \gg 1; \frac{C_b}{C_g} \gg 1$$

$$\frac{v_{out}}{Q_{in}} = \frac{1}{C_f} \cdot \frac{1}{1 + \frac{C_d}{C_b}}$$

$$\text{for } \frac{C_d}{C_b} \gg 1 \rightarrow \frac{v_{out}}{Q_{in}} \approx \frac{1}{C_f} \times \frac{C_b}{C_d}$$

Do we need **feedback**? Not needed but useful; it defines the gain (charge sensitivity) and the response.

**Feedback cannot improve S/N** (it “feeds” back both signal and noise). With feedback this is just a classical Charge Sensitive Amplifier.

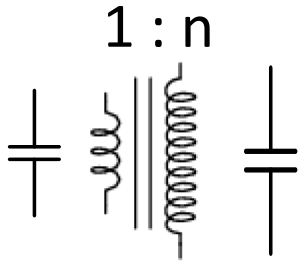
The result:  **$C_b$  has to be larger than  $C_g$ , but can be much smaller than  $C_d$ :**

$$7 \times 2^7 \sqrt{22^7} \text{ fF}$$

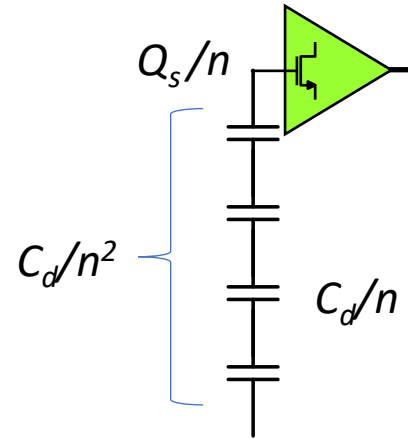
# Toward matching ...

$$ENC = \frac{e_n}{\tau^{1/2}} \left( \frac{C_d}{n} + nC_{gs} \right) \quad n_{opt} = \left( \frac{C_d}{C_{gs}} \right)^{1/2} \quad ENC_{sopt} = 2 \frac{e_n (C_d C_{gs})^{1/2}}{\tau_p^{1/2}}$$

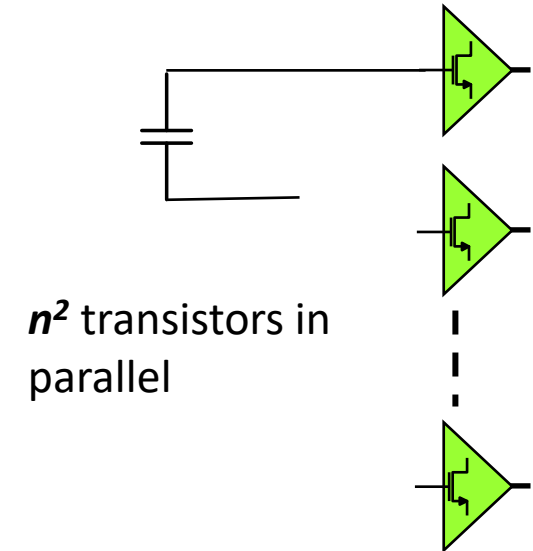
$n$  = transformation ratio for EM and ES transformers = (number of transistors in parallel)<sup>1/2</sup>



EM transformer, the best and proven, but not radio pure



Electrostatic transformer



$n^2$  transistors in parallel

For  $C_d = 10000$  pf:

$$C_g = 25 \text{ pF} \rightarrow n_{opt} = \sqrt{C_d / C_g} \cong 20$$

$$\text{ENC is reduced by: } \frac{1}{2} \sqrt{C_d / C_g} = 10$$

**ES transformer  $n=4$  will improve S/N by a factor of  $\sim 3.95$  ;  $n=2$  by a factor of  $\sim 2$ , compared to parallel connection of SiPMs.**

It would take **16(4)** times as many transistors **and power** for the same result as with ES transformer

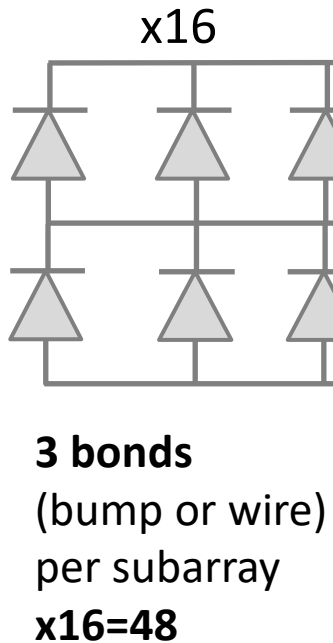
Cannot connect too many in SiPMs in series: excessive high voltage, need of HV capacitor

# SiPM Readout: Interposer and Electronics Daughterboard

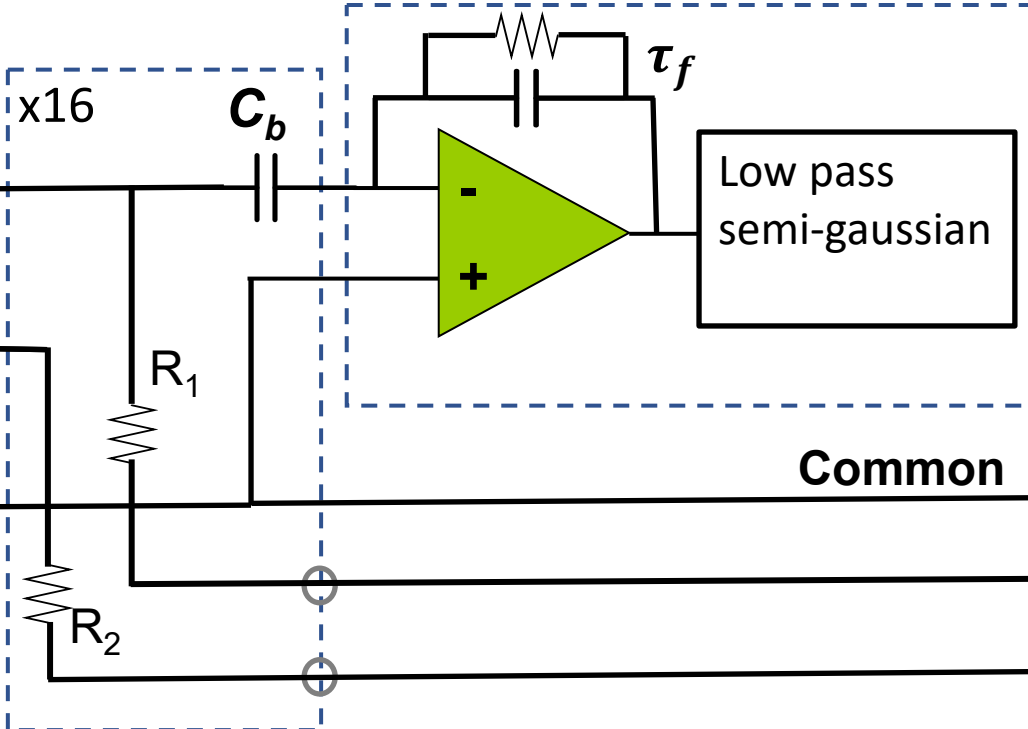
## Two-ASICs approach

### SiPM Interposer

- one of 16 subarrays/tile shown



### LAr ASIC (one of 16 channels) Developed for Dune/Microboone



### ADC-Digital ASIC

ADC  
data serializer  
cable driver  
(pre-emphasis)

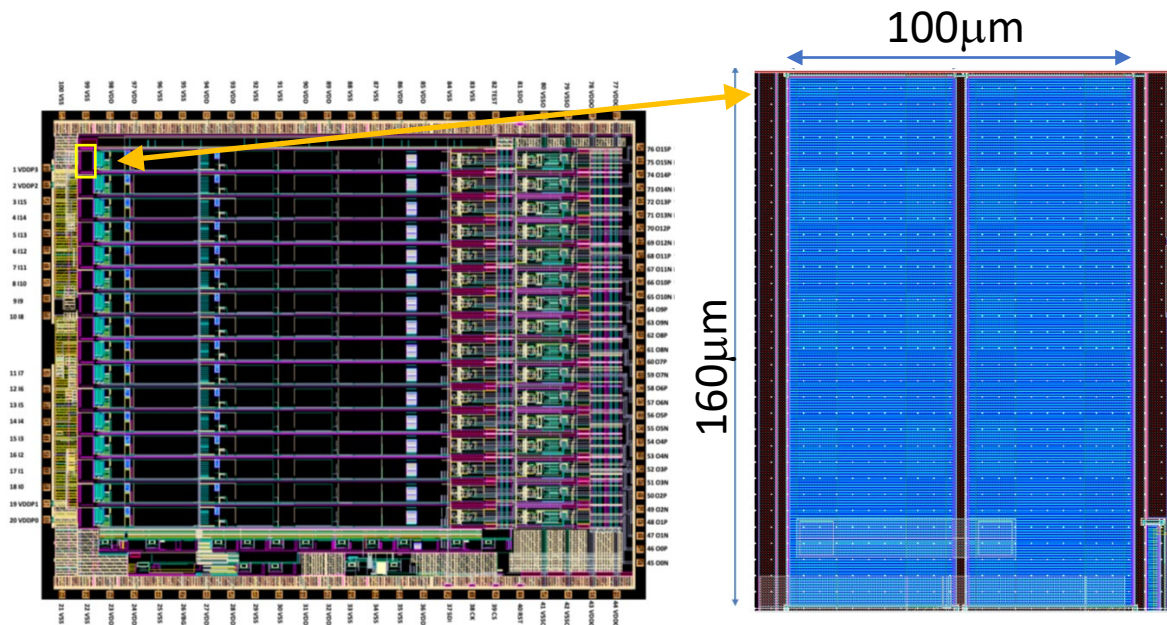
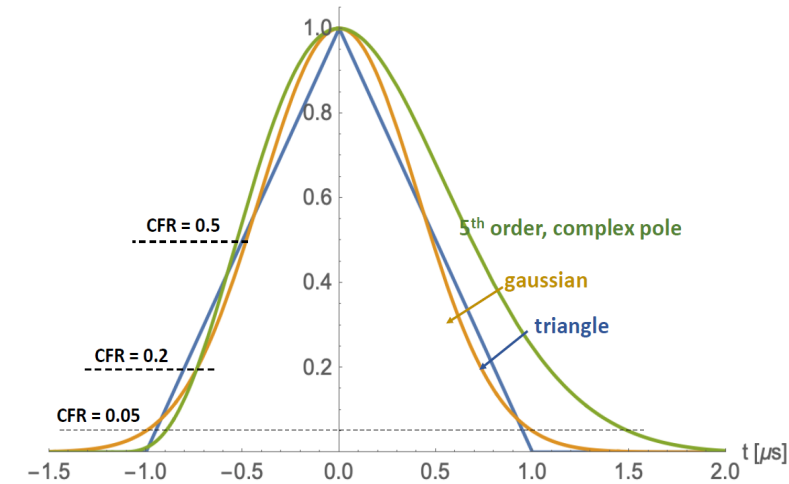
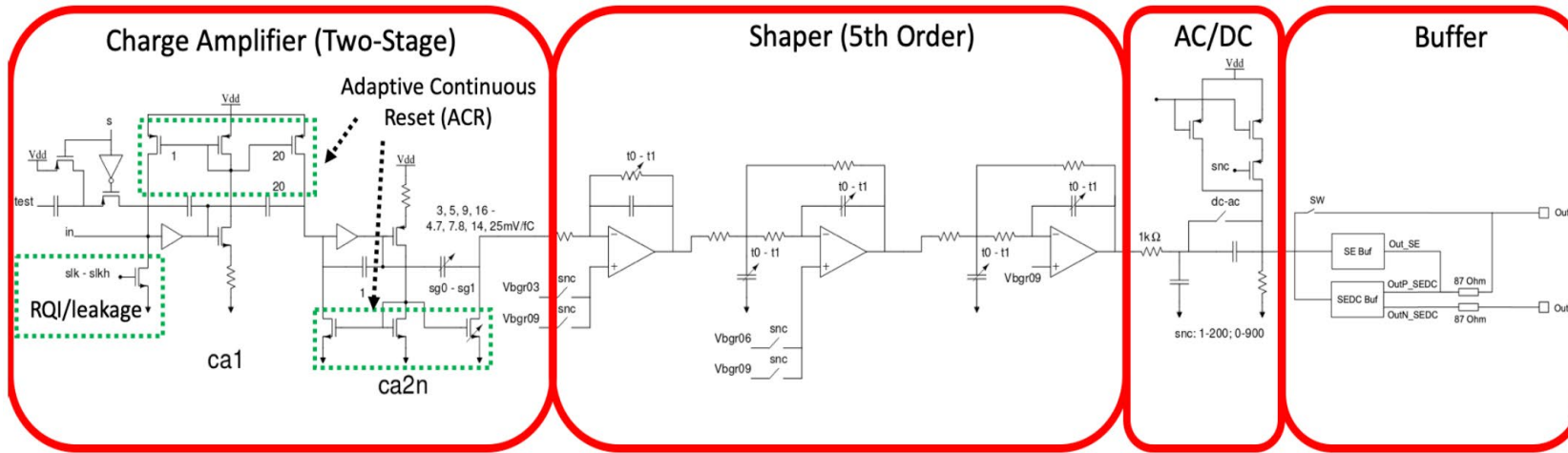
Tile-links connections

One of 16 sets of  $R_1, R_2, C_b$  is shown

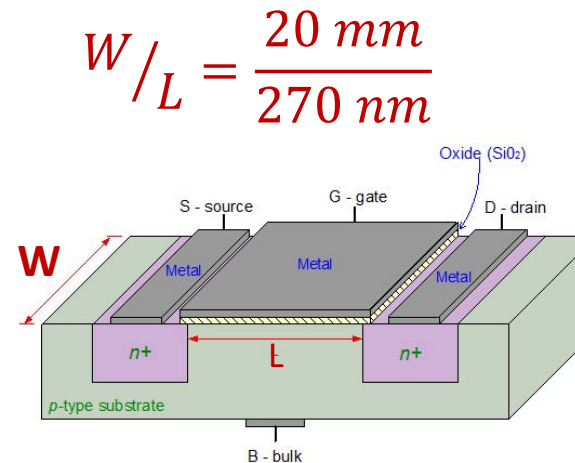
Common for all 24 tiles in a stave  
320 SiPM subarray ("minitiles")



# LArASIC = Antialiasing Filter



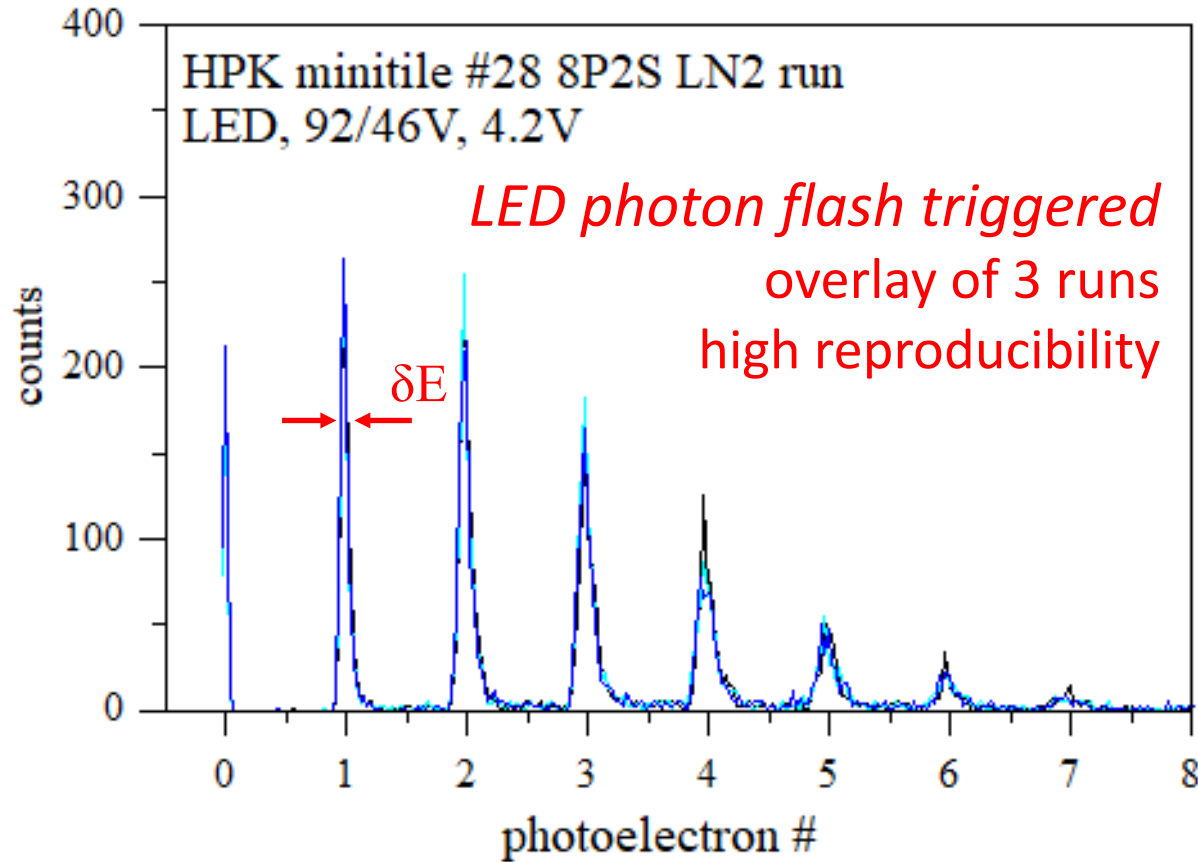
$$160\mu m \times 100\mu m = 16,000\mu m^2$$



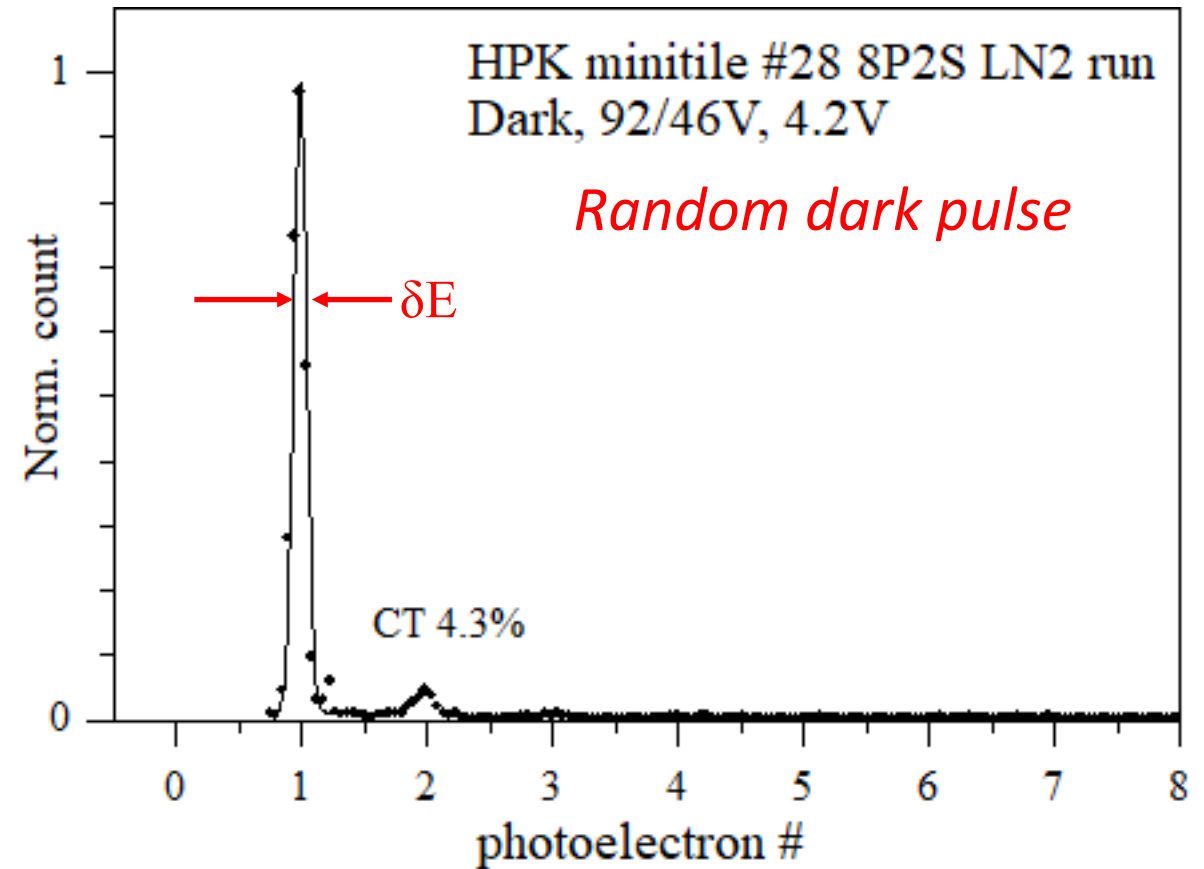
For a very large low noise PMOS transistor  $W \sim 20\text{ mm}$ ,  $L \sim 270\text{ nm}$ ,  $W/L \sim 4 \times 10^4$ ,  $C_g \sim 20\text{ pF}$  ;  
 The transistor can never match a nanofarad SiPM;  
 This very large transistor is a small fraction ( $\sim 1/400$ ) of the SiPM capacitance.



# SiPM Minitile (6 cm<sup>2</sup>) : Charge Histogram, LN<sub>2</sub>

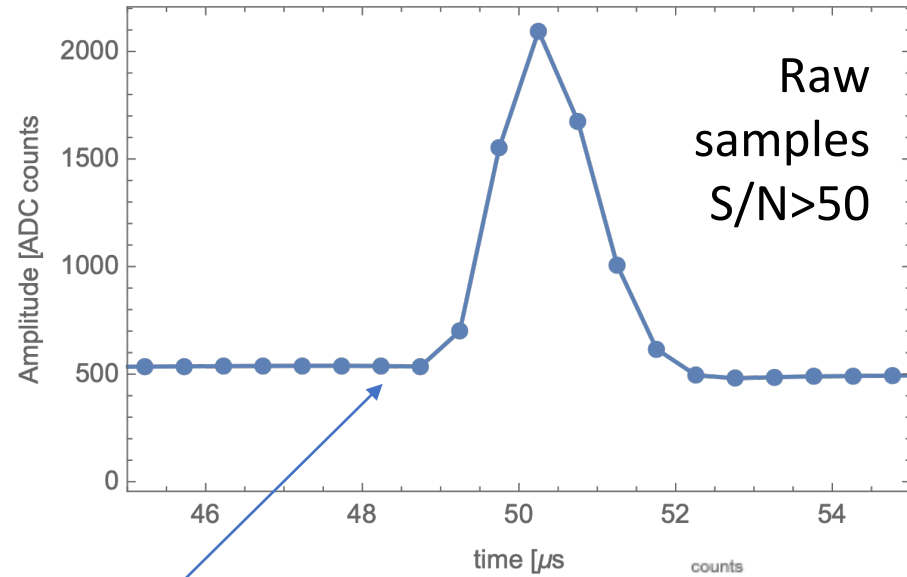


**Photon rate: ~80 Hz (trigger rate 100 Hz)**  
**1-pe resolution ( $\delta E$ ): 3 to 3.5% rms**

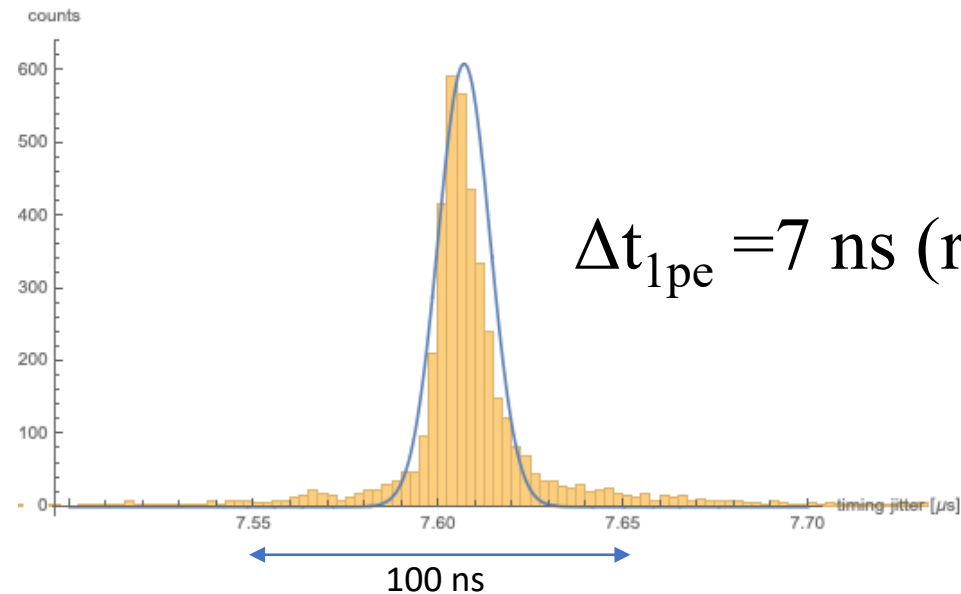
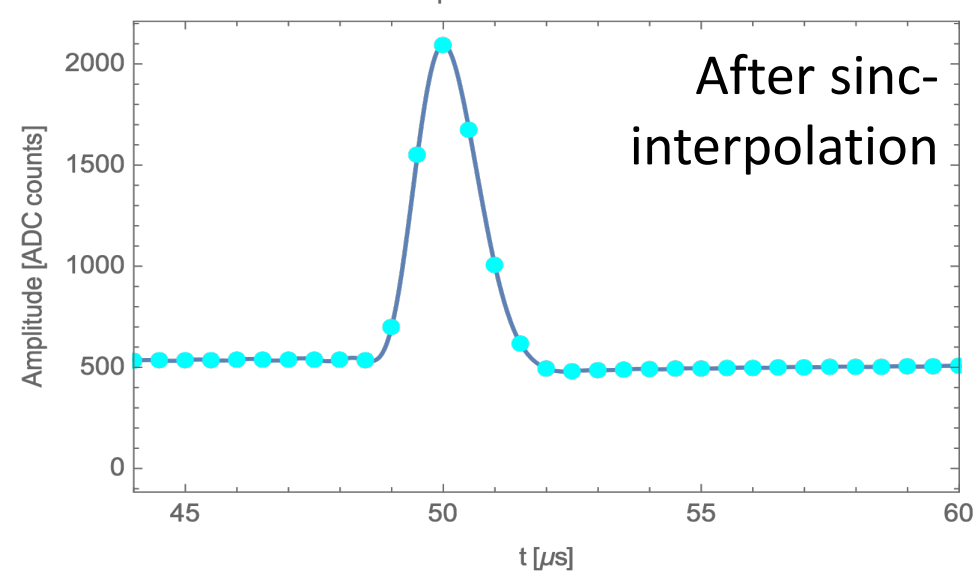


**DCR: ~96 Hz (0.17 Hz/mm<sup>2</sup>)**  
**1-pe resolution ( $\delta E$ ): ~5% rms**

# Waveform reconstruction and single-photon timing resolution (SPTR)



10  $\mu$ s = 20  
samples at 2Msps

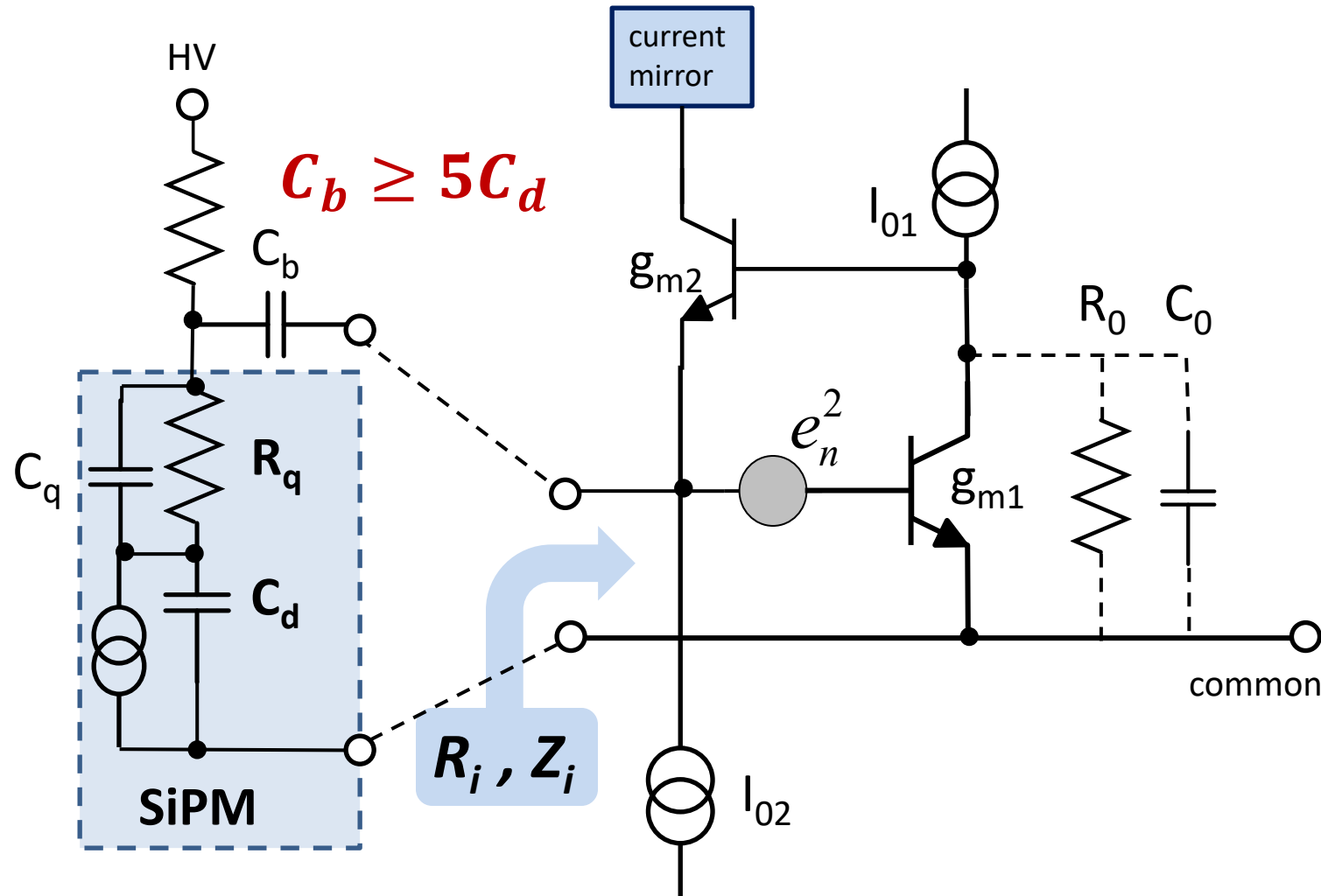


Using sinc-interpolation + ‘digital’ constant fraction discriminator, leads to a low timing error (SPTR)

# Summary

- In a conventional approach using a “current amplifier”, or any other, both the signal and series noise are affected equally by amplifier feedback, and S/N ratio remains unaffected by feedback.
- With large SiPM capacitance grossly mismatched to even the largest input transistor, transfer of charge from SiPM via a large (de)coupling capacitor ( $C_b > C_d$ , i.e., strong coupling) does not contribute to S/N.
- Due to a large mismatch, **a weak coupling between the SiPM and the input transistor is sufficient**, where  $C_d > C_b \gg C_g$ . Most appropriate configuration for realization of this concept is a charge sensitive amplifier (CSA), coupled to SiPMs by a decoupling capacitor an order of magnitude smaller than SiPM capacitance ( $C_b \sim 200\text{-}500\text{pF}$  for 5-10 nF SiPM subarray)
- The LAr FE ASIC for MicroBooNE, protoDUNE and SBND (“LArASIC”), has the required characteristics, and it has made possible experimental verification of the noise calculation. SiPM response, S/N, and timing resolution have been demonstrated.

# SiPM Readout by “Current Feedback Amplifier”?



- A large (de)coupling capacitor  $C_b$  is required.
- There are additional noise sources in the “Current Feedback Amplifier” besides the input transistor